



1A NPN SURFACE MOUNT TRANSISTOR

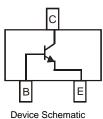
Features

- **Epitaxial Planar Die Construction**
- Ideal for Low Power Amplification and Switching
- High Collector Current Rating
- Complementary Version Available (DPBT8105)
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green Device" (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current - Continuous	Ιc	1	А
Peak Pulse Collector Current	I _{CM}	2	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1) @ $T_A = 25^{\circ}C$	PD	600	mW
Thermal Resistance, Junction to Ambient (Note 1) @ $T_A = 25^{\circ}C$	$R_{ ext{ heta}JA}$	209	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	S₀

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)					·
Collector-Base Breakdown Voltage	V _{(BR)CBO}	80		V	$I_{C} = 100 \mu A, I_{E} = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	60		V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5		V	$I_{E} = 100 \mu A, I_{C} = 0$
Collector Cutoff Current	I _{CBO}		100	nA	$V_{CB} = 60V, I_E = 0$
Collector Cutoff Current	I _{CES}		100	nA	$V_{CES} = 60V$
Emitter Cutoff Current	I _{EBO}	_	100	nA	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h _{FE}	100 100 80 30	 300 	—	$\begin{split} I_{C} &= 1 \text{mA}, \ V_{CE} = 5 \text{V} \\ I_{C} &= 500 \text{mA}, \ V_{CE} = 5 \text{V} \\ I_{C} &= 1 \text{A}, \ V_{CE} = 5 \text{V} \\ I_{C} &= 2 \text{A}, \ V_{CE} = 5 \text{V} \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.25 0.5	V	$I_{C} = 500$ mA, $I_{B} = 50$ mA $I_{C} = 1$ A, $I_{B} = 100$ mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}		1.1	V	$I_{\rm C} = 1$ A, $I_{\rm B} = 100$ mA
Base-Emitter Turn On Voltage	V _{BE(ON)}		1.0	V	$I_{C} = 1A, V_{CE} = 5V$
SMALL SIGNAL CHARACTERISTICS				•	·
Output Capacitance	C _{obo}		10	pF	V _{CB} = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f _T	150		MHz	$V_{CE} = 10V, I_{C} = 50mA, f = 100MHz$

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

2. No purposefully added lead.

4. Short duration pulse test used to minimize self-heating effect.

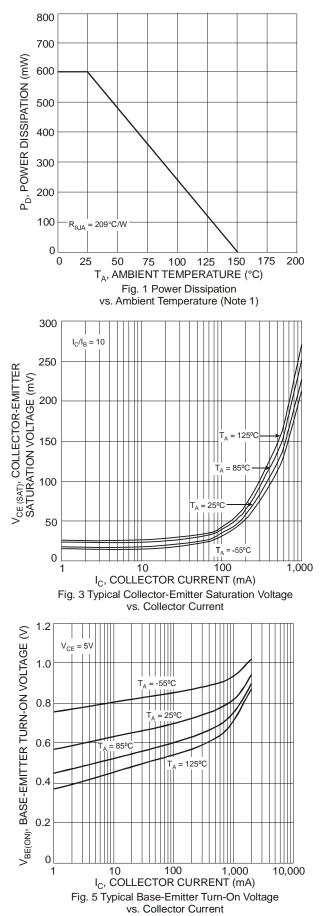
DNBT8105 Document number: DS30513 Rev. 9 - 2

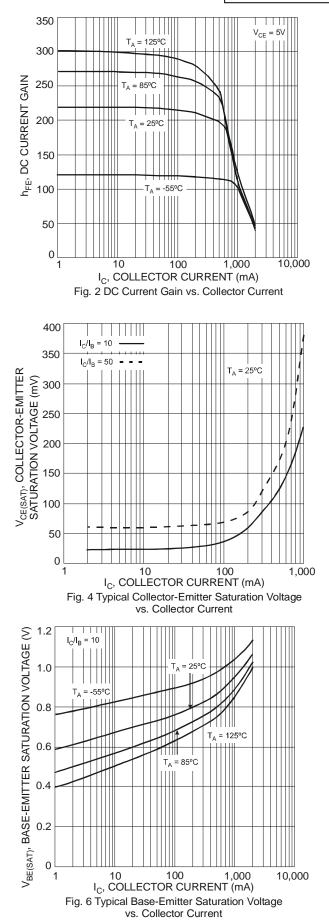
1 of 4 www.diodes.com

Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php. 3.

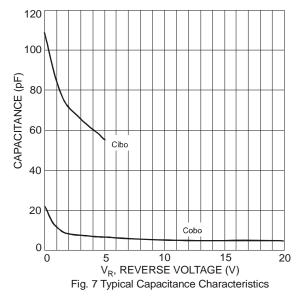












Ordering Information (Note 5)

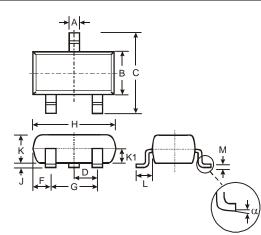
Part Number	Case	Packaging
DNBT8105-7	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

			[K81	MY	K81 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: S = 2005) M = Month (ex: 9 = September)						
Date Code Key				\Box								
Year	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	R	S	Т	U	V	W	Х	Y	Z	А	В	С
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	Jan	1.60	ITAI	Арі	inay	Juli	Jui	лиу	oep	001	1101	000
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions

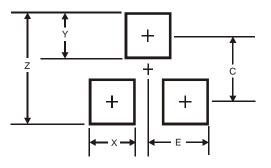


SOT-23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
C	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
М	0.085	0.18	0.11		
α	0°	8°	-		
All	All Dimensions in mm				

DNBT8105



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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